

General Description

The Sanrise SRC60R030FBS is a high voltage power MOSFET, fabricated using advanced super junction technology. The resulting device has extremely low on resistance, low gate charge and fast switching time, making it especially suitable for applications which require superior power density and outstanding efficiency.

The SRC60R030FBS break down voltage is 600V and it has a high rugged avalanche characteristics.

The SRC60R030FBS is available in TO-247 package.

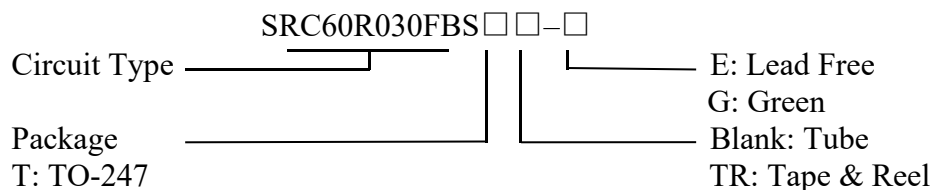
Features

- Ultra Low $R_{DS(ON)} = 30m\Omega @ V_{GS} = 10V$.
- $V_{ds@T_{jmax}} = 650V$.
- Ultra Low Gate Charge, $Q_g = 187nC$ typ.
- Fast switching capability
- Robust design with better EAS performance
- Low Q_{rr}
- Non-automotive Qualified
- Ultra-fast body diode

Application

- High Performance Application
- High Power Application
- EV Charger

Ordering Information



Symbol

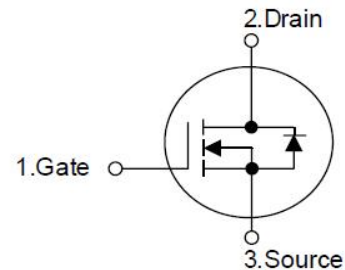


Figure 1 Symbol of SRC60R030FBS

Package Type

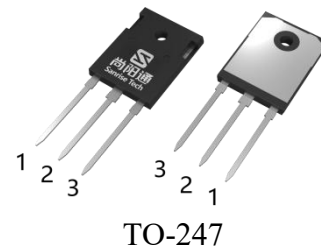


Figure 2 Package Type of SRC60R030FBS

Package	Part Number	Marking ID	Packing Type
TO-247	SRC60R030FBST-G	SRC60R030FBSTG	Tube

Absolute Maximum Ratings^{Note 1}

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage (static)		V_{GSS}	±20	V
Gate-Source Voltage (dynamic), AC ($f > 1$ Hz)		V_{GSS}	±30	V
Power Dissipation($T_C=25^{\circ}C, TO-247$)		P_{tot}	500	W
Continuous Drain Current	$T_C=25^{\circ}C$	I_D	91	A
	$T_C=100^{\circ}C$		57	
	$T_C=125^{\circ}C$		41	
Pulsed Drain Current (Note 2)		I_{DM}	273	A
Avalanche Energy, Single Pulse (Note 3)		E_{AS}	200	mJ
Avalanche Energy, Single Pulse (Note 4)		E_{AS}	1889	mJ
Avalanche Energy, Repetitive (Note 2)		E_{AR}	1.0	mJ
Avalanche Current, Repetitive (Note 2)		I_{AR}	6.4	A
Continuous Diode Forward Current		I_S	91	A
Diode Pulse Current		$I_{S,PULSE}$	273	A
MOSFET dv/dt Ruggedness, $V_{DS} \leq 480V$		dv/dt	120	V/ns
Reverse Diode dv/dt, $V_{DS} \leq 480V, I_{SD} \leq I_D$		dv/dt	50	V/ns
Operating Junction Temperature		T_J	150	°C
Storage Temperature		T_{STG}	-55 to 150	°C
Lead Temperature (Soldering, 10 sec)		T_{LEAD}	260	°C

Note:

- Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
- Repetitive Rating: Pulse width limited by maximum junction temperature
- $I_{AS}=6.4A, V_{DD}=60V, R_G=25\Omega$, Starting $T_J=25^{\circ}C$. Finish goods test condition.
- $I_{AS}=19.4A, V_{DD}=60V, R_G=25\Omega$, Starting $T_J=25^{\circ}C$. Typical Eas.

Thermal characteristics

Parameter		Symbol	Min	Typ	Max	Unit
Thermal resistance, Junction-to-Case	TO-247	R_{thJC}			0.25	°C /W
Thermal resistance, Junction-to-Ambient	TO-247	R_{thJA}			60	°C /W

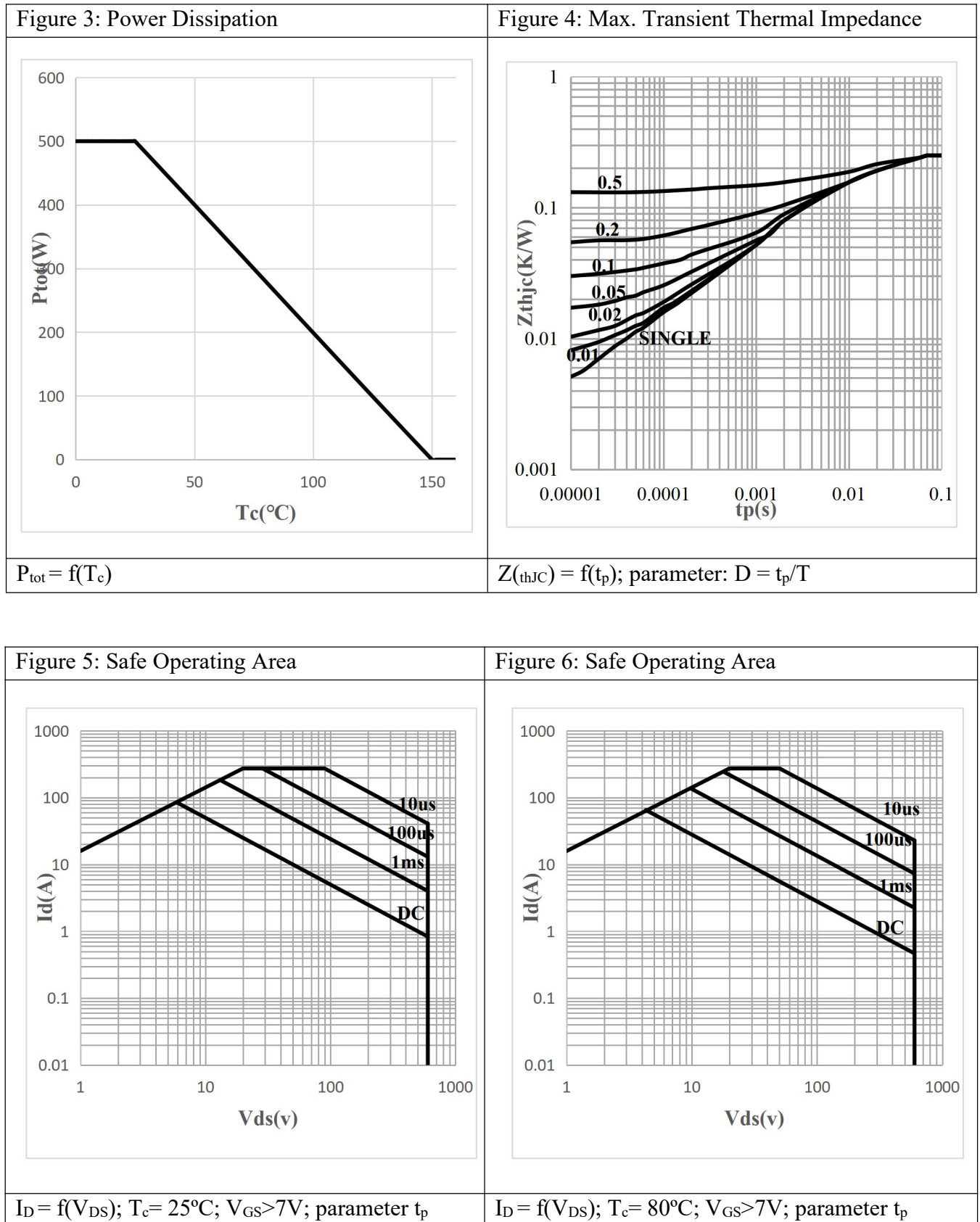
Electrical Characteristics

 T_J = 25°C, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Statistic Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	600			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	uA	
Gate-Body Leakage Current	Forward	I _{GSSF}	V _{GS} =20V, V _{DS} =0V		100	nA	
	Reverse	I _{GSSR}	V _{GS} =-20V, V _{DS} =0V		-100		
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =2.2mA	3.0	4.0	5.0	V	
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =34A		23.7	30	mΩ	
Gate Resistance	R _G	f=1MHz, Open Drain		1.0		Ω	
Dynamic Characteristics							
Input Capacitance	C _{ISS}	V _{DS} =400V, V _{GS} =0V, f=100kHz		8.6		nF	
Output Capacitance	C _{OSS}				165		pF
Effective output capacitance, energy related ^{NOTE5}	C _{O(er)}	V _{GS} =0V, V _{DS} =0...400V		222		pF	
Effective output capacitance, time related ^{NOTE6}	C _{O(tr)}				1354		
Turn-on Delay Time	t _{d(on)}	V _{DD} =400V, I _D =34A R _G =3Ω, V _{GS} =12V		66		ns	
Rise Time	t _r			39			
Turn-off Delay Time	t _{d(off)}			103			
Fall Time	t _f			10			
Gate Charge Characteristics							
Gate to Source Charge	Q _{gs}	V _{DD} =400V, I _D =34A V _{GS} =0 to 10V		70		nC	
Gate to Drain Charge	Q _{gd}			69.5			
Gate Charge Total	Q _g			187			
Gate Plateau Voltage	V _{plateau}			6.9		V	
Reverse Diode Characteristics							
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _{SD} =34A		0.9	1.1	V	
Reverse Recovery Time	t _{rr}	V _R =400V, I _F =34A dI _F /dt=100A/us		197		ns	
Reverse Recovery Charge	Q _{rr}				2.4		uC
Peak Reverse Recovery Current	I _{rrm}				20		A

Note:

- C_{O(er)} is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 480V
- C_{O(tr)} is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 480 V

Typical Performance Characteristics


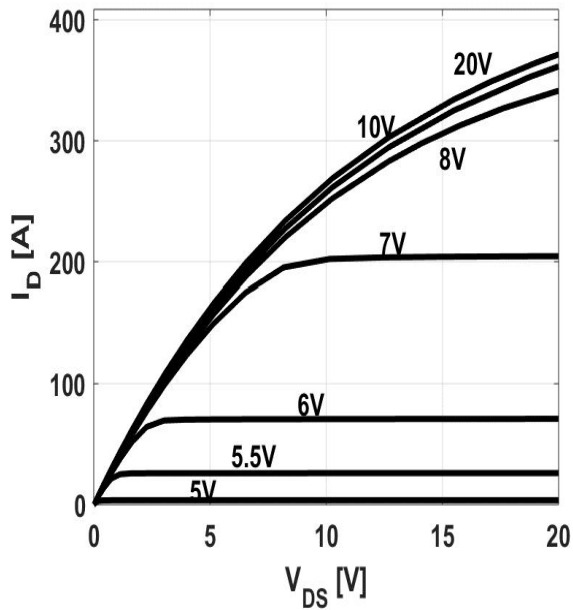
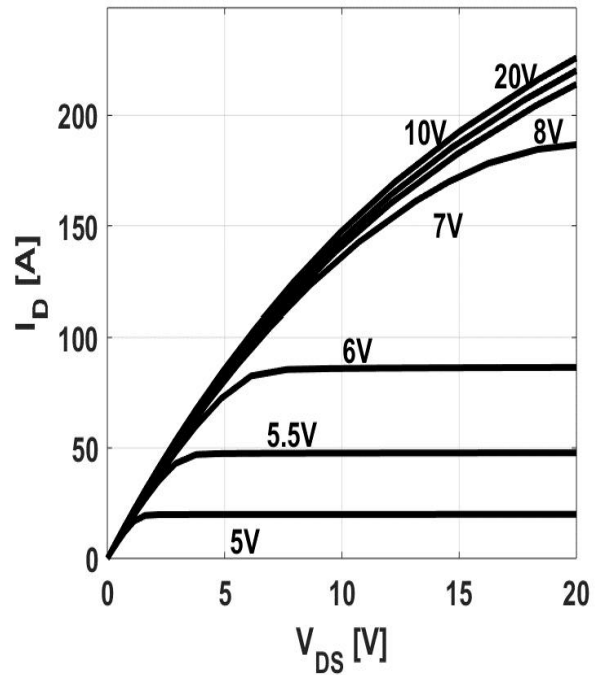
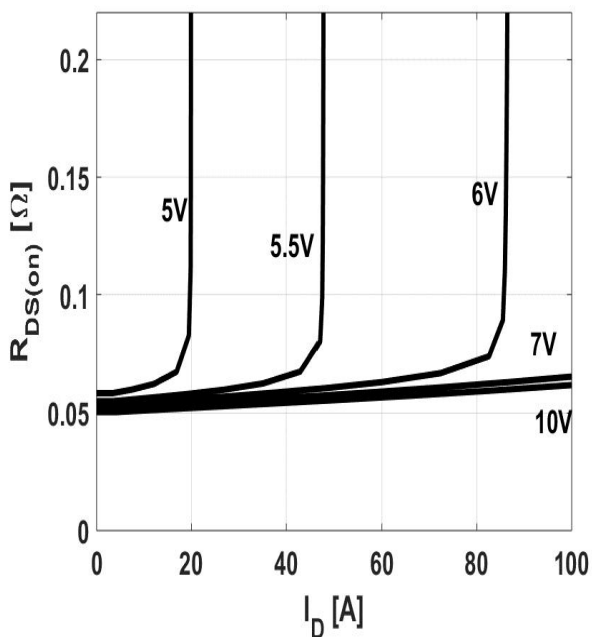
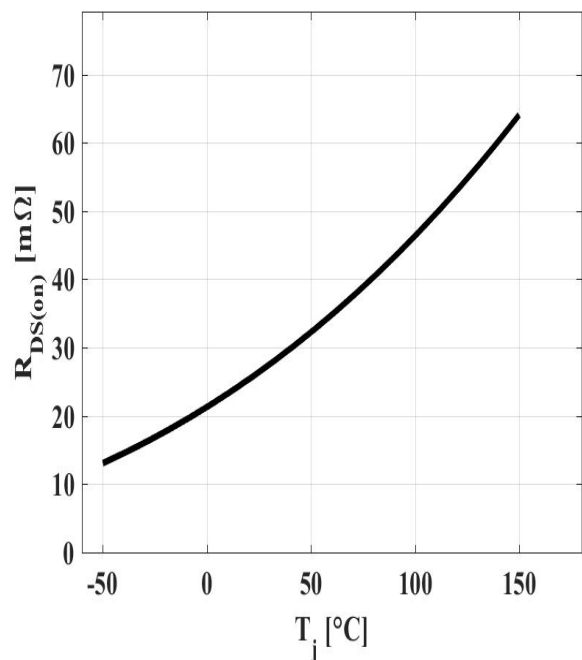
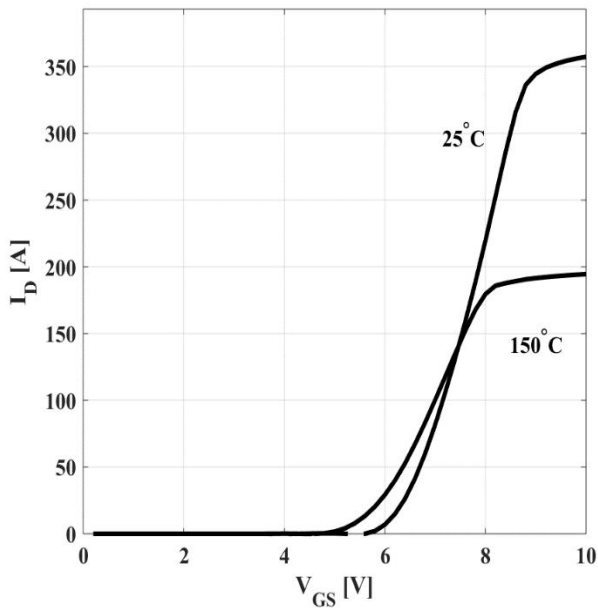
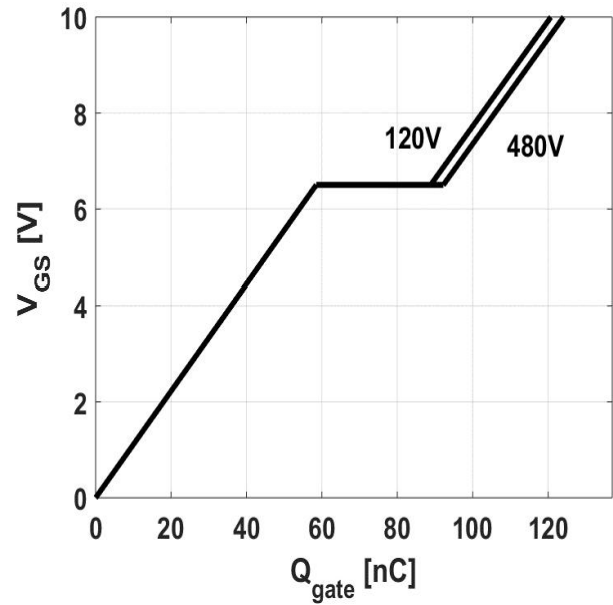
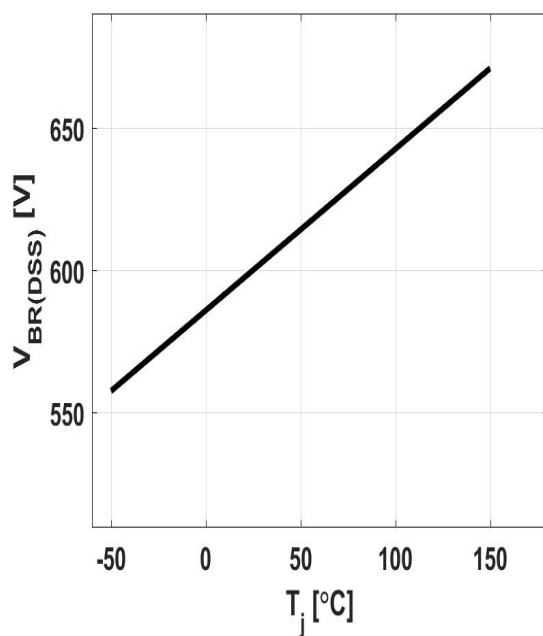
30mΩ, 600V, Super Junction N-Channel Power MOSFET
SRC60R030FBS
Figure 7: Typ. Output Characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 8: Typ. Output Characteristics

 $I_D = f(V_{DS}); T_j = 125^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 9: Typ. Drain-Source On-State Resistance

 $R_{DS(on)} = f(I_D); T_j = 125^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 10: Typ. Drain-Source On-State Resistance

 $R_{DS(on)} = f(T_j); I_D = 34\text{A}; V_{GS} = 10\text{V}$

Figure 11: Typ. Transfer Characteristics


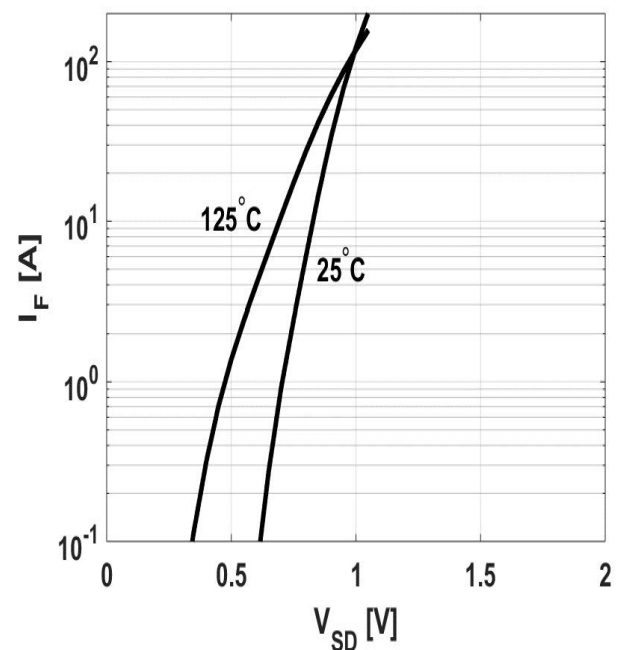
$$I_D = f(V_{GS}); V_{DS} = 20V$$

Figure 12: Typ. Gate Charge


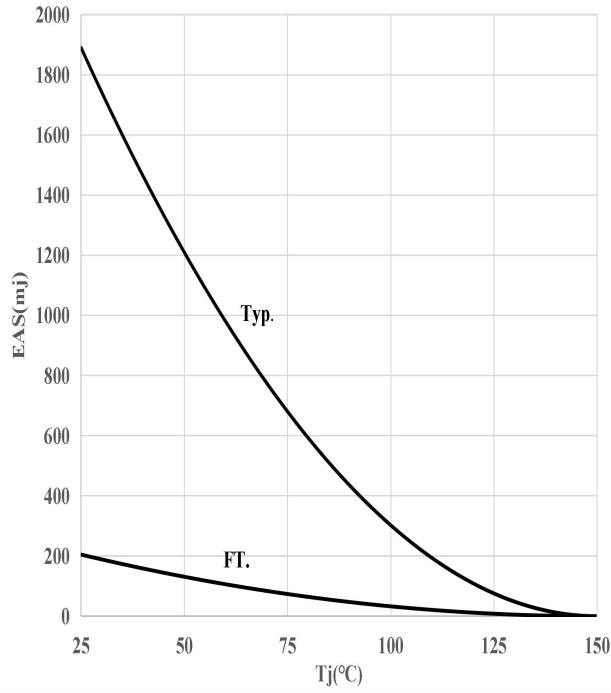
$$V_{GS} = f(Q_{gate}), I_D = 34A \text{ pulsed}$$

Figure 13: Drain-Source Breakdown Voltage


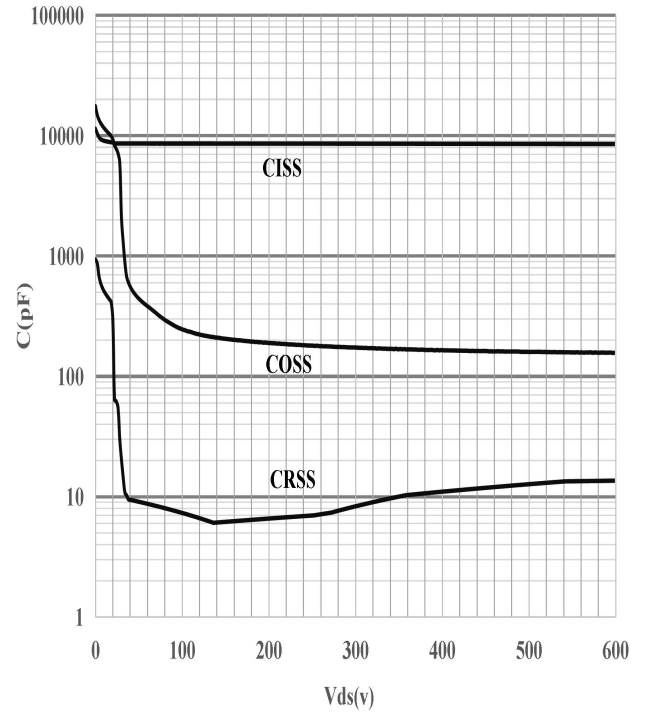
$$\text{Minimum } V_{BR(DSS)} = f(T_j); I_D = 10mA$$

Figure 14: Forward Characteristics of Reverse Diode


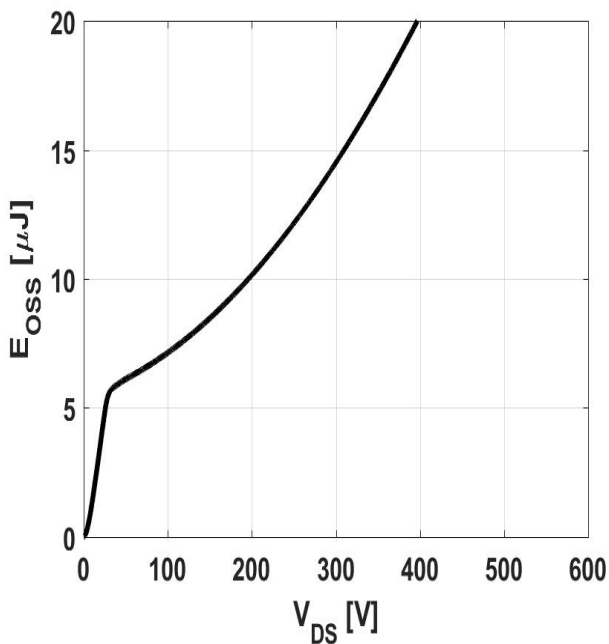
$$I_F = f(V_{SD}); \text{parameter: } T_j$$

Figure 15: Avalanche Energy


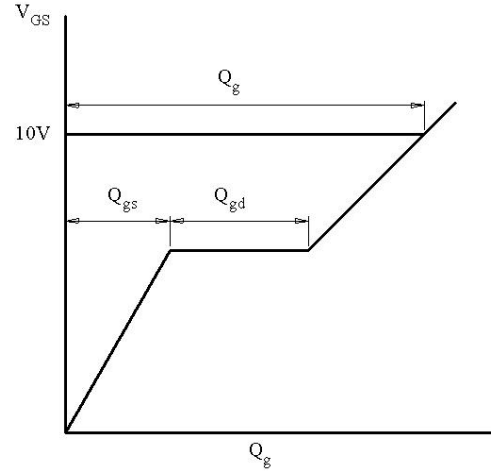
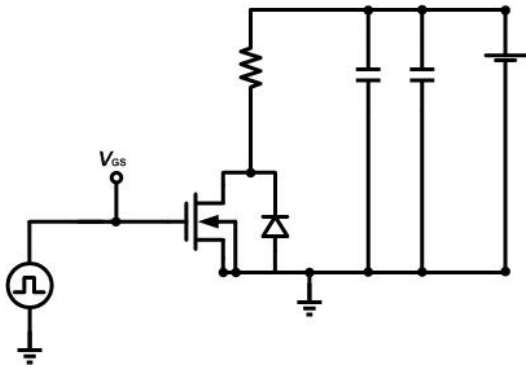
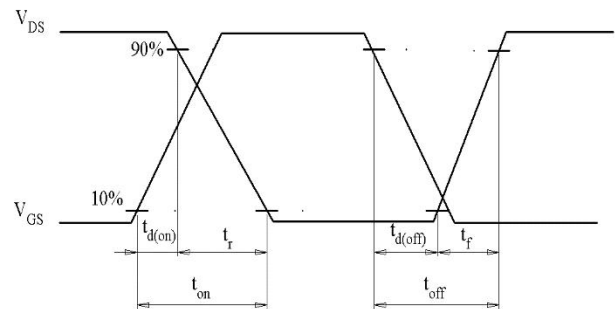
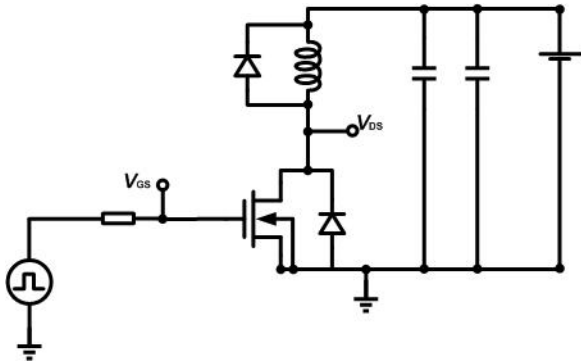
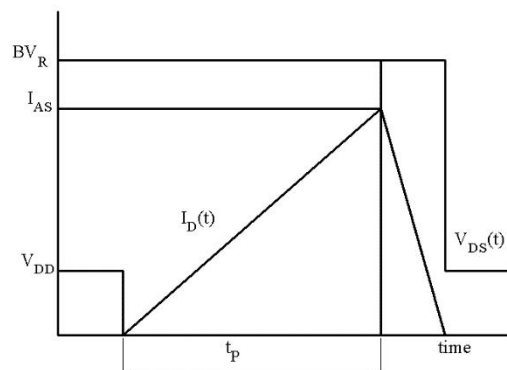
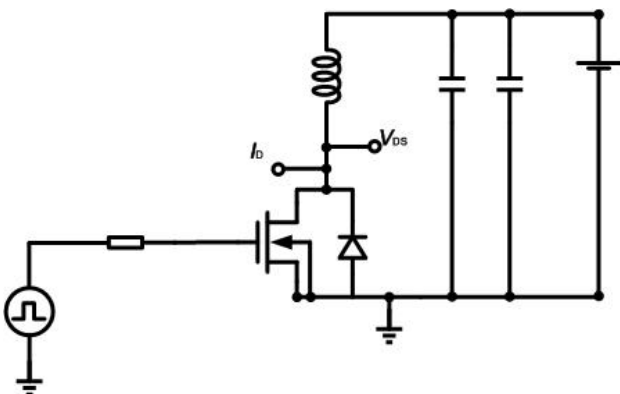
$$E_{AS}=f(T_j); V_{DD}=60V$$

Figure 16: Typ. Capacitances


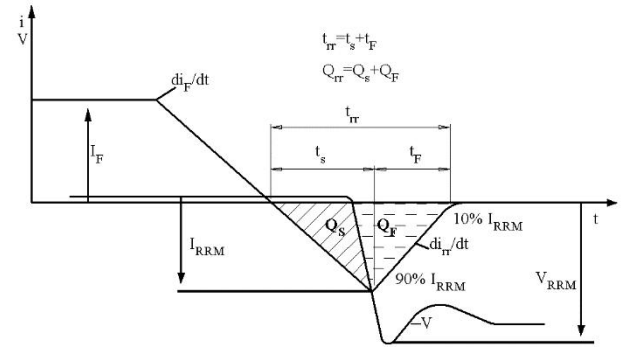
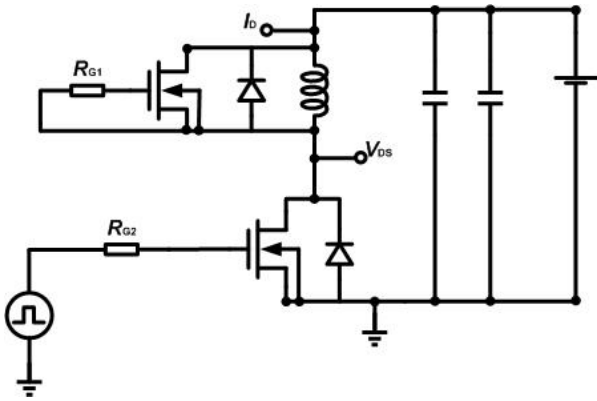
$$C=f(V_{DS}); V_{GS}=0; f=100kHz$$

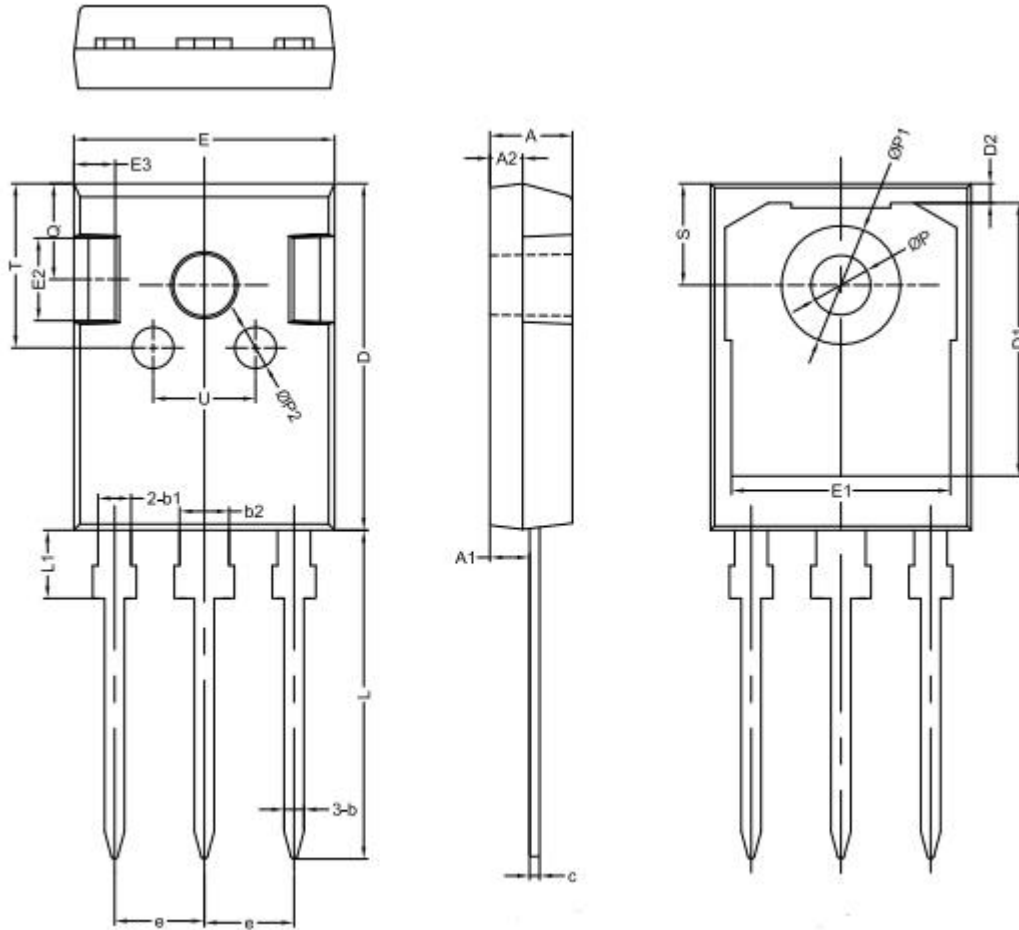
Figure 17: COSS Stored Energy


$$E_{OSS}=f(V_{DS})$$

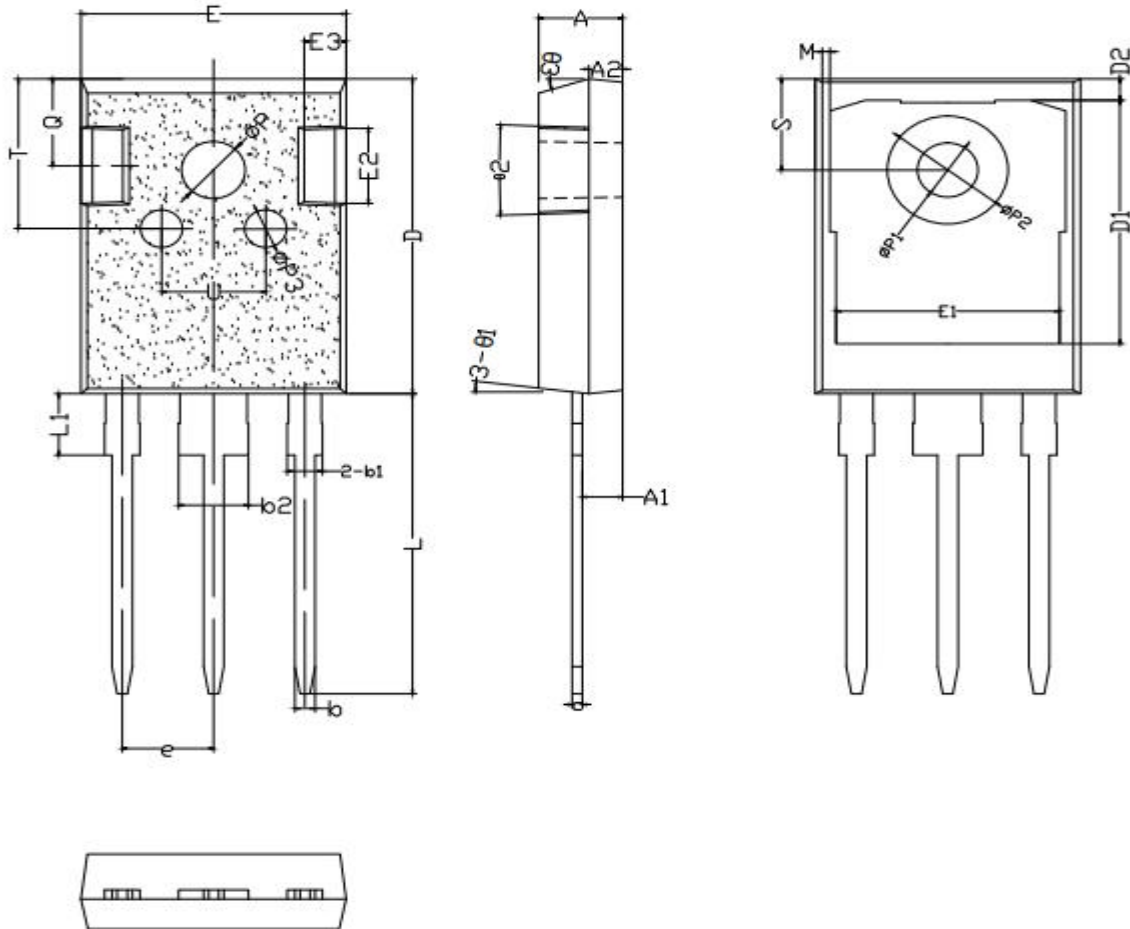
Test Circuits
1. Gate Charge Test Circuit & Waveform

2. Switch Time Test Circuit

3. Unclaimed Inductive Switching Test Circuit & Waveforms


4. Test Circuit and Waveform for Diode Characteristics

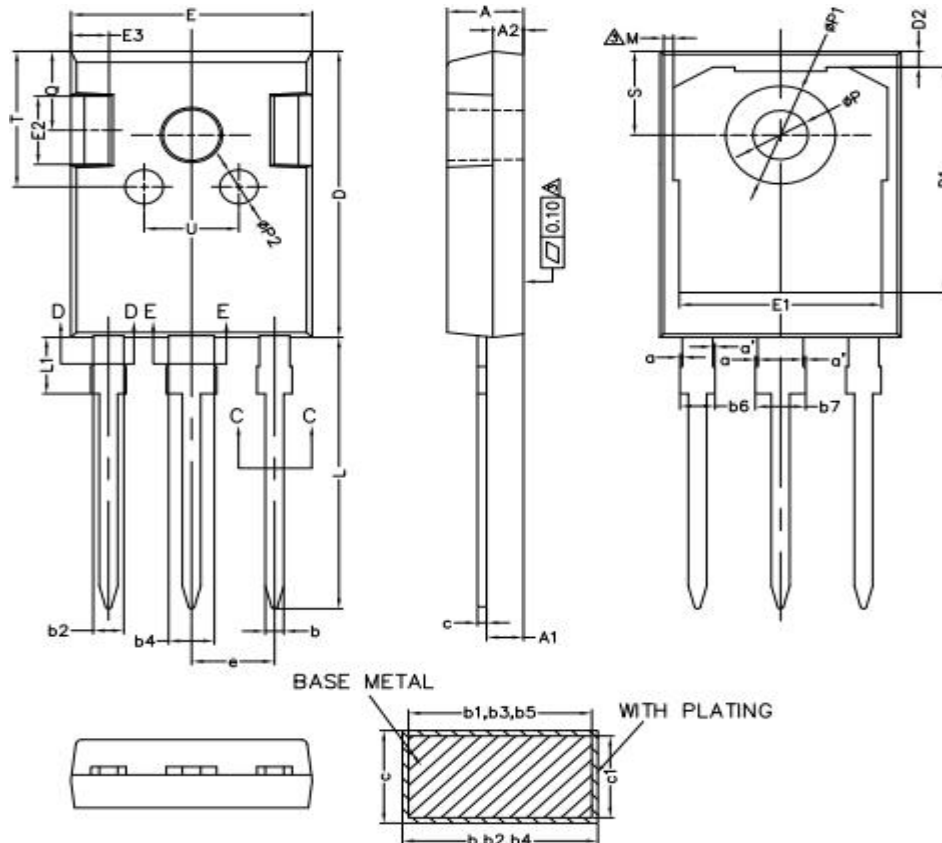


Mechanical Dimensions
TO-247(Package 1)
Unit: mm


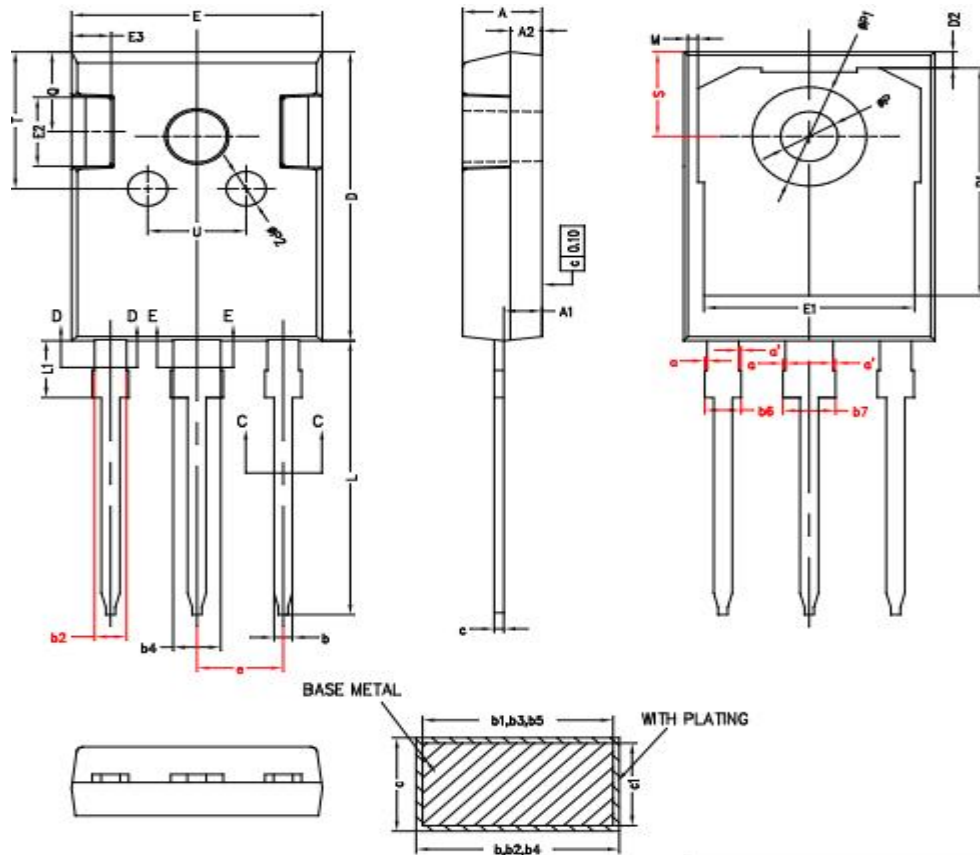
Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.80	5.00	5.20	E1	-	13.30	-
A1	2.21	2.41	2.61	E2	-	5.00	-
A2	1.90	2.00	2.10	E3	-	2.50	-
b	1.10	1.20	1.35	L	19.42	19.92	20.42
b1	-	2.00	-	L1	-	4.13	-
b2	-	3.00	-	P	3.50	3.60	3.70
c	0.55	0.60	0.75	P1	-	7.19	-
D	20.80	21.00	21.20	P2	-	2.50	-
D1	-	16.55	-	Q	-	5.80	-
D2	-	1.20	-	S	6.05	6.15	6.25
E	15.60	15.80	16.0	T	-	10.00	-
U	-	6.20	-	e	-	5.44	-

Mechanical Dimensions
TO-247(Package 2)
Unit: mm


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.90	5.00	5.10	E1	13.10	13.25	13.40
A1	2.31	2.41	2.51	E2	4.85	4.95	5.10
A2	1.90	2.00	2.10	E3	2.40	2.50	2.60
b	1.15	1.20	1.25	L	19.80	19.98	20.15
b1	1.95	2.10	2.25	L1	-	-	4.30
b2	2.95	3.10	3.25	ΦP	3.60	3.70	3.80
c	0.55	0.60	0.65	ΦP1	3.40	3.50	3.60
D	20.90	21.00	21.10	ΦP2	6.90	7.10	7.30
D1	16.35	16.55	16.75	Q	5.60	5.80	6.00
D2	1.05	1.20	1.35	S	6.05	6.15	6.25
E	15.70	15.80	15.90	T	9.80	10.00	10.20
U	6.00	6.20	6.40	e	5.40	5.44	5.48
Θ1	5°	7°	9°	ΦP3	2.40	2.50	2.60
Θ2	1°	3°	5°	Θ3	13°	15°	17°

Mechanical Dimensions
TO-247(Package 3)
Unit: mm


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.90	5.00	5.10	c1	0.58	0.60	0.62
A1	2.31	2.41	2.51	D	20.90	21.00	21.10
A2	1.90	2.00	2.10	D1	16.25	16.55	16.85
b	1.16	-	1.26	D2	1.05	1.20	1.35
b1	1.15	1.20	1.22	E	15.70	15.80	15.90
b2	1.96	-	2.06	E1	13.10	13.30	13.50
b3	1.95	2.00	2.02	E2	4.90	5.00	5.10
b4	2.96	-	3.06	E3	2.40	2.50	2.60
b5	2.95	3.00	3.02	e	5.34	5.44	5.54
b6	-	-	2.25	L	19.80	19.92	20.10
b7	-	-	3.25	L1	3.95	4.13	4.30
c	0.59	-	0.66	M	0.35	-	0.95
P	3.50	3.60	3.70	P1	7.00	-	7.40
P2	2.40	2.50	2.60	Q	5.60	-	6.00
S	6.05	6.15	6.25	T	9.80	-	10.20
U	6.00	-	6.40	a	0	-	0.15
a'	0	-	0.15				

Mechanical Dimensions
TO-247(Package 4)
Unit: mm


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.90	5.00	5.10	E2	4.90	5.00	5.10
A1	2.31	2.41	2.51	E3	2.40	2.50	2.60
A2	1.90	2.00	2.10	e	5.34	5.44	5.54
b	1.12	-	1.22	L	19.80	19.92	20.10
b1	1.11	1.16	1.18	L1	3.95	4.13	4.30
b2	1.96	-	2.06	P	3.50	3.60	3.70
c	0.59	-	0.66	P1	7.00	-	7.40
D	20.90	21.00	21.10	P2	2.40	2.50	2.60
D1	16.25	16.55	16.85	Q	5.60	-	6.00
D2	1.05	1.20	1.35	S	6.05	6.15	6.25
E	15.70	15.80	15.90	T	9.80	-	10.20
E1	13.10	13.30	13.50	U	6.00	-	6.40
b3	1.95	2.00	2.02	b6	-	-	2.25
b4	2.96	-	3.06	b7	-	-	3.25
b5	2.95	3.00	3.02	c1	0.58	0.60	0.62
M	0.35	-	0.95	a	0	-	0.15
a'	0	-	0.15				



TM

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